



40V 3.5A DOUBLE POWER HALF BRIDGE

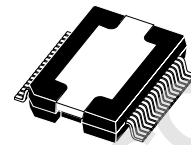
- MINIMUM INPUT OUTPUT PULSE WIDTH DISTORTION
- 200mΩ R_{dsON} COMPLEMENTARY DMOS OUTPUT STAGE
- CMOS COMPATIBLE LOGIC INPUTS
- THERMAL PROTECTION
- THERMAL WARNING OUTPUT
- UNDER VOLTAGE PROTECTION

DESCRIPTION

STA501 is a monolithic dual half bridge stage in Multipower BCD Technology.

The device is particularly designed to make the output stage of a mono All-Digital High Efficiency

MULTIPOWER BCD TECHNOLOGY

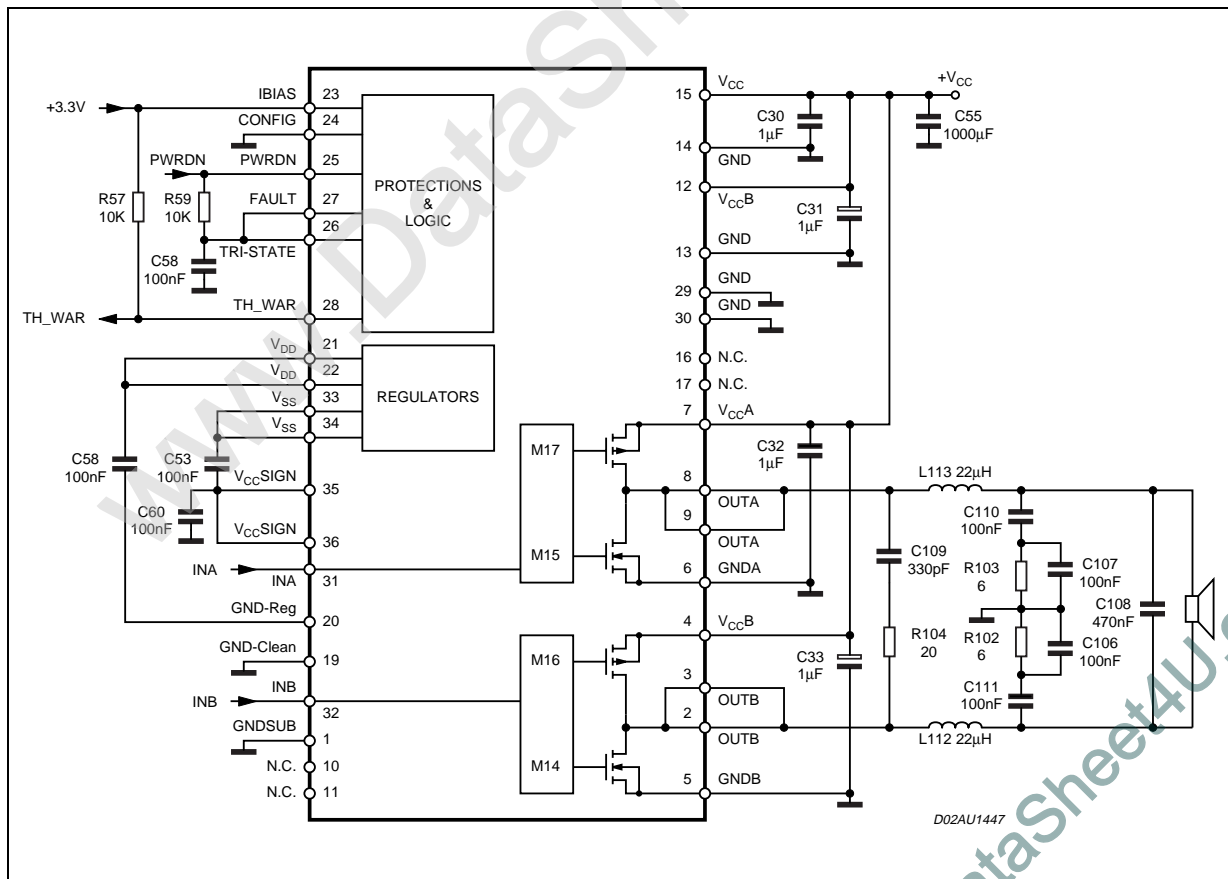


PowerSO36

ORDERING NUMBER: STA501

(DDX™) amplifier capable to deliver 50W @ THD = 10% at V_{CC} 30V output power on 8Ω load. The input pins have threshold proportional to I_{bias} pin voltage.

AUDIO APPLICATION CIRCUIT



STA501

PIN FUNCTION

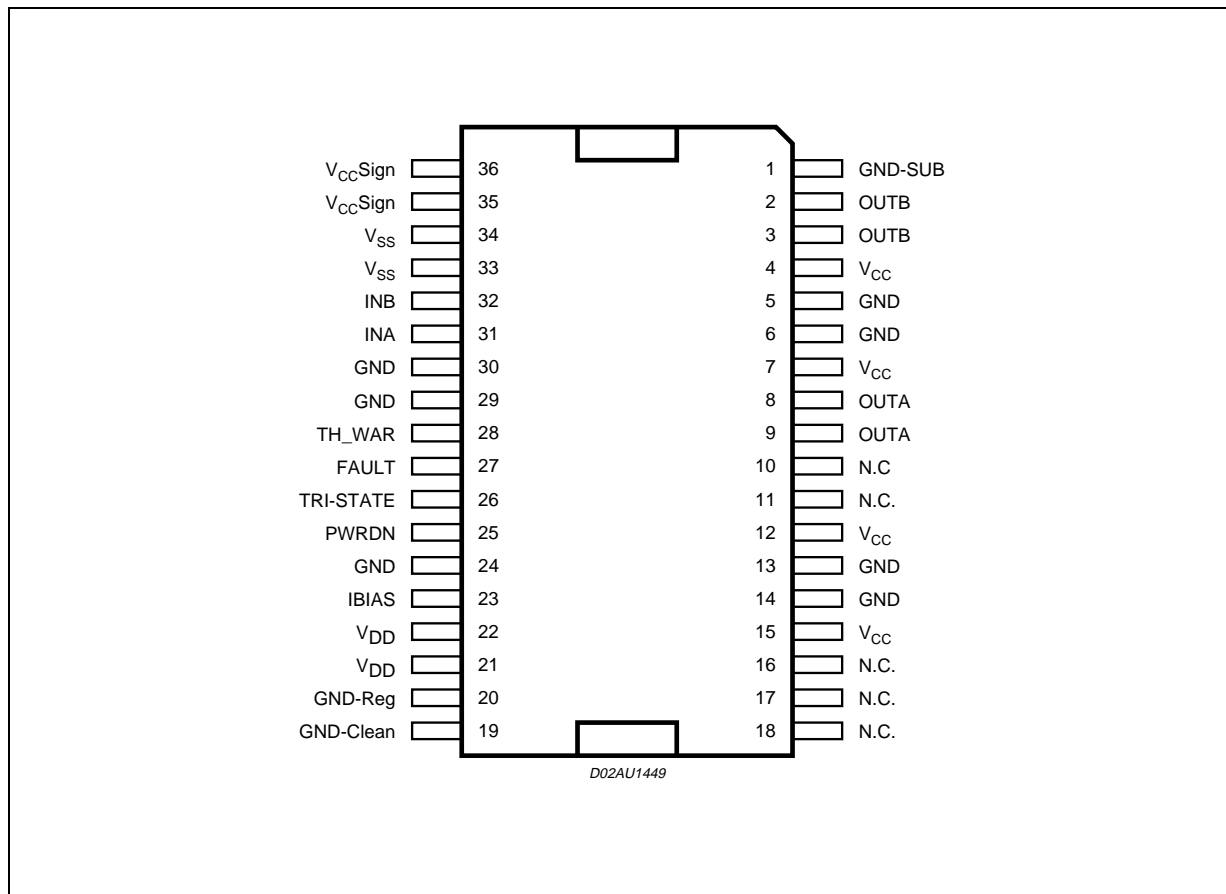
| N° | Pin | Description |
|---------|-----------|------------------------------------|
| 1 | GND-SUB | Substrate ground |
| 35 ; 36 | Vcc Sign | Signal Positive Supply |
| 15 | Vcc | Positive Supply |
| 12 | Vcc | Positive Supply |
| 7 | Vcc | Positive Supply |
| 4 | Vcc | Positive Supply |
| 14 | GND | Negative Supply |
| 13 | GND | Negative Supply |
| 6 | GND | Negative Supply |
| 5 | GND | Negative Supply |
| 16 ; 17 | N.C. | |
| 10 ; 11 | N.C. | |
| 8 ; 9 | OUTA | Output half bridge |
| 2 ; 3 | OUTB | Output half bridge |
| 29 | GND | |
| 30 | GND | |
| 31 | INA | Input of half bridge |
| 32 | INB | Input of half bridge |
| 21 ; 22 | Vdd | 5V Regulator referred to ground |
| 33 ; 34 | Vss | 5V Regulator referred to +Vcc |
| 25 | PWRDN | Stand-by pin |
| 26 | TRI-STATE | Hi-Z pin |
| 27 | FAULT | Fault pin advisor |
| 24 | GND | |
| 28 | TH-WAR | Thermal warning advisor |
| 19 | GND-clean | Logical ground |
| 23 | IBIAS | High logical state setting voltage |
| 18 | NC | Not connected |
| 20 | GND-Reg | Ground for regulator Vdd |

FUNCTIONAL PIN STATUS

| PIN NAME | Logical value | IC -STATUS |
|-----------|---------------|---|
| FAULT | 0 | Fault detected (Short circuit, or Thermal ..) |
| FAULT * | 1 | Normal Operation |
| TRI-STATE | 0 | All powers in Hi-Z state |
| TRI-STATE | 1 | Normal operation |
| PWRDN | 0 | Low absorption |
| PWRDN | 1 | Normal operation |
| THWAR | 0 | Temperature of the IC =130C |
| THWAR* | 1 | Normal operation |

* : The pin is open collector. To have the high logic value, it needs to be pulled up by a resistor.

PIN CONNECTION



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------------------------------|-----------------------------------|------------|------|
| V _{CE} | DC Supply Voltage (Pin 4,7,12,15) | 40 | V |
| V _{max} | Maximum Voltage on pins 23 to 32 | 5.5 | V |
| T _{op} | Operating Temperature Range | 0 to 70 | °C |
| T _{stg} , T _j | Storage and Junction Temperature | -40 to 150 | °C |

THERMAL DATA

| Symbol | Parameter | Min. | Typ. | Max. | Unit |
|---------------------|---|------|------|------|------|
| T _{j-case} | Thermal Resistance Junction to Case (thermal pad) | | | 2.5 | °C/W |
| T _{jSD} | Thermal shut-down junction temperature | | 150 | | °C |
| T _{warn} | Thermal warning temperature | | 130 | | °C |
| t _{hSD} | Thermal shut-down hysteresis | | 25 | | °C |

ELECTRICAL CHARACTERISTICS (I_{bias} = 3.3V; V_{cc} = 30V; T_{amb} = 25°C unless otherwise specified)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------------|--|---|--------------------------------|------|--------------------------------|------|
| R _{dsON} | Power Pchannel/Nchannel MOSFET RdsON | I _d =1A | | 200 | 270 | mΩ |
| I _{dss} | Power Pchannel/Nchannel leakage I _{dss} | V _{cc} =35V | | | 50 | μA |
| g _N | Power Pchannel RdsON Matching | I _d =1A | 95 | | | % |
| g _P | Power Nchannel RdsON Matching | I _d =1A | 95 | | | % |
| Dt _s | Low current Dead Time (static) | see test circuit no.1; see fig. 1 | | 10 | 20 | ns |
| Dt _d | High current Dead Time (dynamic) | L=22μH; C = 470nF; R _I = 8 Ω I _d =3.5A; see fig. 3 | | | 50 | ns |
| t _{d ON} | Turn-on delay time | Resistive load | | | 100 | ns |
| t _{d OFF} | Turn-off delay time | Resistive load | | | 100 | ns |
| t _r | Rise time | Resistive load | | | 25 | ns |
| t _f | Fall time | Resistive load; as fig. 1 | | | 25 | ns |
| V _{CC} | Supply voltage operating voltage | | 10 | | 36 | V |
| V _{IN-H} | High level input voltage | | | | I _{bias} /2 +300mV | V |
| V _{IN-L} | Low level input voltage | | I _{bias} /2 -300mV | | | V |
| I _{IN-H} | Hi level Input current | Pin voltage = I _{bias} | | 1 | | μA |

ELECTRICAL CHARACTERISTICS (continued)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|------------------------|---|--|------|------|------|------|
| I _{IN-L} | Low level input current | Pin voltage = 0.3V | | 1 | | μA |
| I _{PWRDN-H} | Hi level PWRDN pin input current | I _{bias} = 3.3V | | 35 | | μA |
| V _L | Low logical state voltage V _L (pin PWRDN, TRISTATE) (note 1) | I _{bias} = 3.3V | 0.8 | | | V |
| V _H | High logical state voltage V _H (pin PWRDN, TRISTATE) (note 1) | I _{bias} = 3.3V | | | 1.7 | V |
| I _{VCC-PWRDN} | Supply Current from V _{cc} in Power Down | PWRDN = 0 | | | 3 | mA |
| I _{FAULT} | Output Current pins FAULT -TH-WARN when FAULT CONDITIONS | V _{pin} = 3.3V | | 1 | | mA |
| I _{VCC-hiz} | Supply current from V _{cc} in Tri-state | V _{cc} =30V; Tri-state=0 | | 22 | | mA |
| I _{VCC} | Supply current from V _{cc} in operation (both channel switching) | Input pulse width = 50% Duty; Switching Frequency = 384Khz; No LC filters; | | 80 | | mA |
| I _{VCC-q} | I _{sc} (short circuit current limit) | | 3.5 | 6 | 8 | A |
| I _{OUT-SH} | Undervoltage protection threshold | | | 7 | | V |
| V _{OV} | Output minimum pulse width | No Load | 70 | | 150 | ns |

Notes: 1. The following table explains the V_L, V_H variation with I_{bias}

| I _{bias} | V _L min | V _H max | Unit |
|-------------------|--------------------|--------------------|------|
| 2.7 | 0.7 | 1.5 | V |
| 3.3 | 0.8 | 1.7 | V |
| 5 | 0.85 | 1.85 | V |

LOGIC TRUTH TABLE (see fig. 2)

| TRI-STATE | INA | INB | Q1 | Q2 | Q3 | Q4 | OUTPUT MODE |
|-----------|-----|-----|-----|-----|-----|-----|-------------|
| 0 | x | x | OFF | OFF | OFF | OFF | Hi-Z |
| 1 | 0 | 0 | OFF | OFF | ON | ON | DUMP |
| 1 | 0 | 1 | OFF | ON | ON | OFF | NEGATIVE |
| 1 | 1 | 0 | ON | OFF | OFF | ON | POSITIVE |
| 1 | 1 | 1 | ON | ON | OFF | OFF | Not used |

Figure 1. Test Circuit.

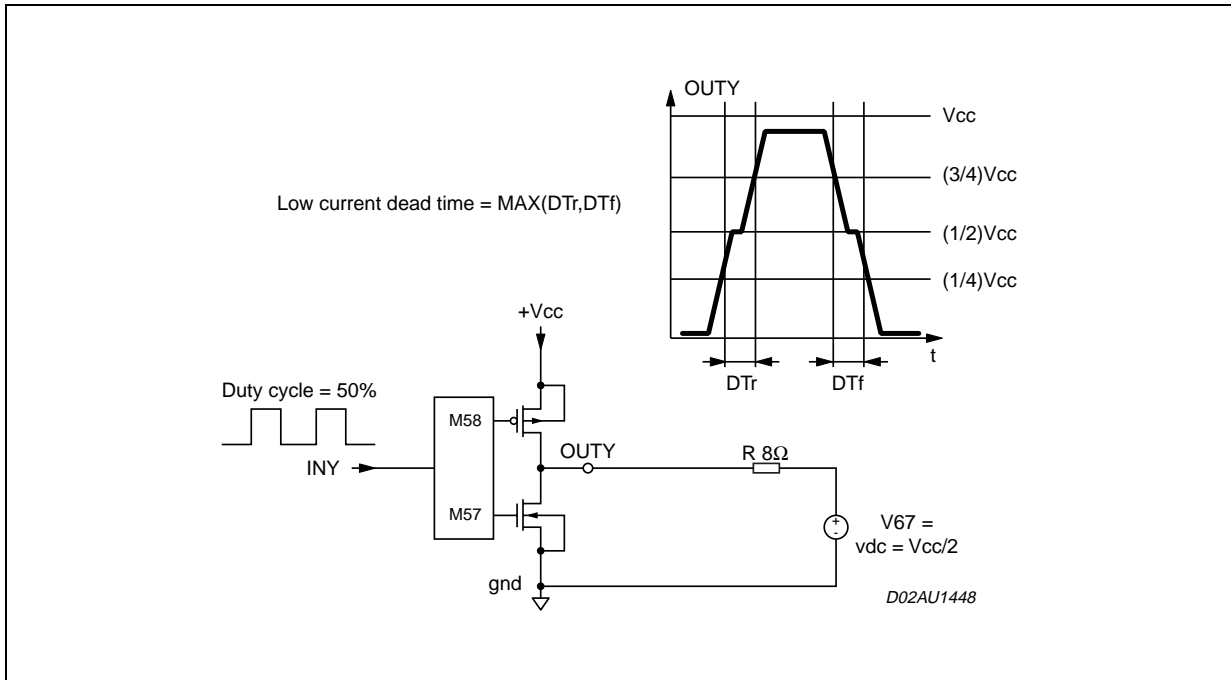


Figure 2.

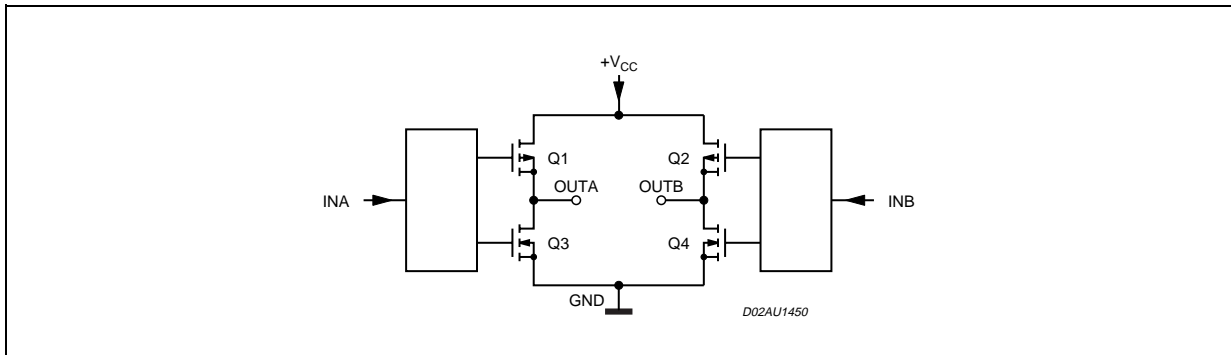
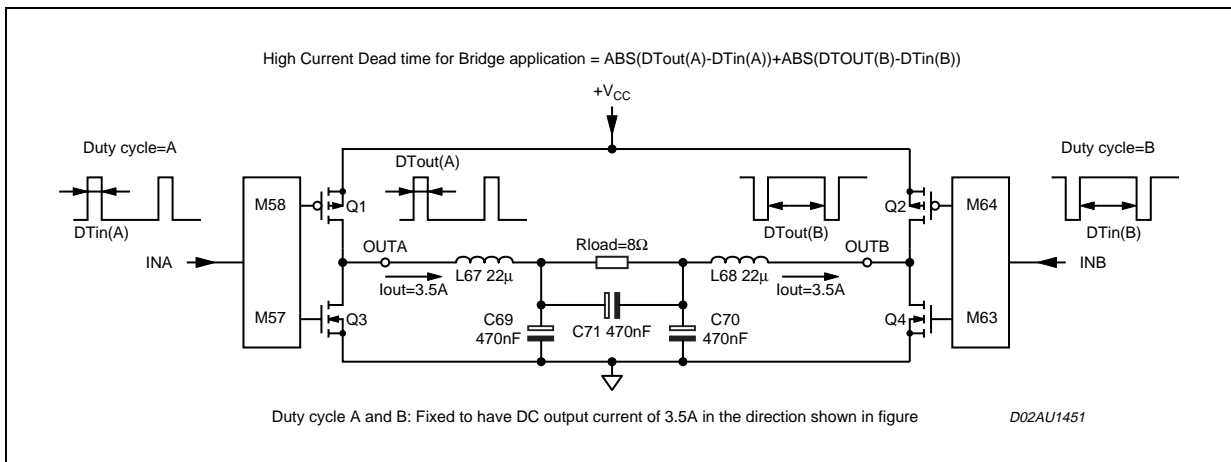


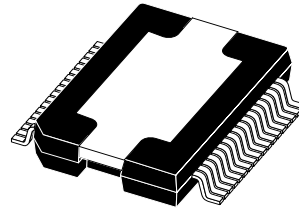
Figure 3.



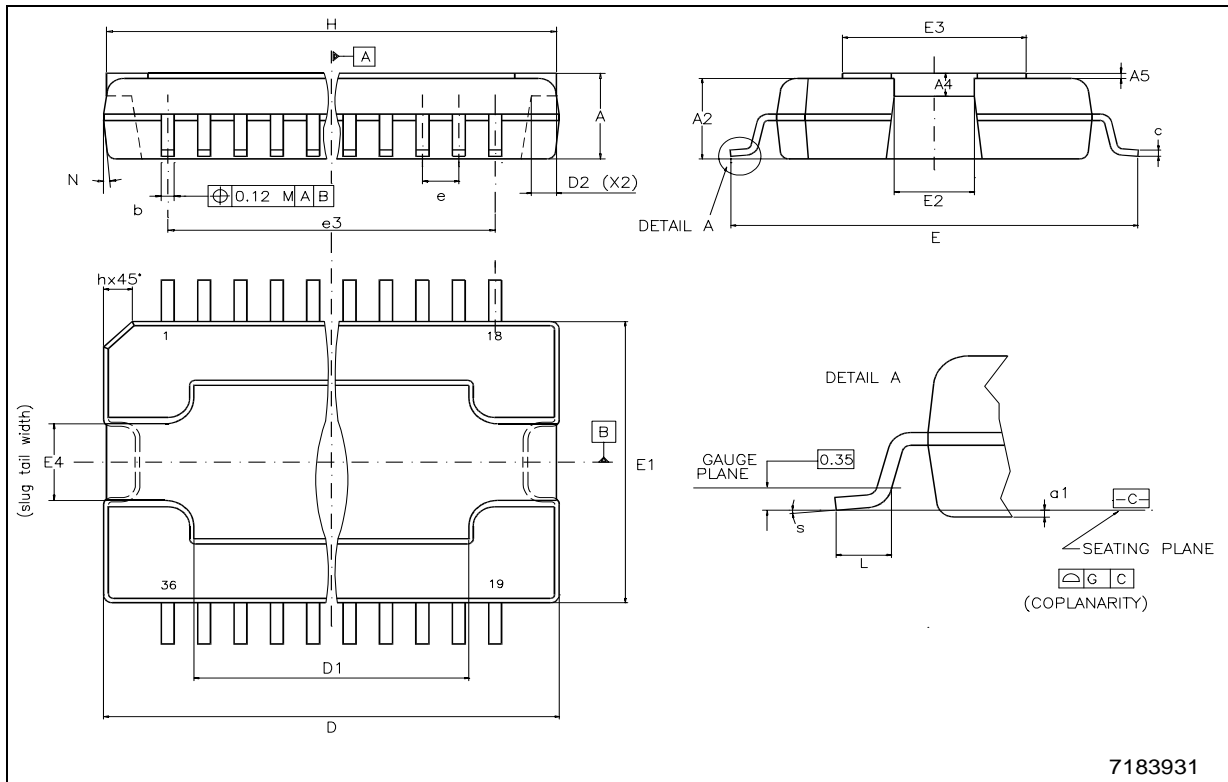
| DIM. | mm | | | inch | | |
|------|-----------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 3.25 | | 3.5 | 0.128 | | 0.138 |
| A2 | | | 3.3 | | | 0.13 |
| A4 | 0.8 | | 1 | 0.031 | | 0.039 |
| A5 | | 0.2 | | | 0.008 | |
| a1 | 0 | | 0.075 | 0 | | 0.003 |
| b | 0.22 | | 0.38 | 0.008 | | 0.015 |
| c | 0.23 | | 0.32 | 0.009 | | 0.012 |
| D | 15.8 | | 16 | 0.622 | | 0.630 |
| D1 | 9.4 | | 9.8 | 0.37 | | 0.38 |
| D2 | | 1 | | | 0.039 | |
| E | 13.9 | | 14.5 | 0.547 | | 0.57 |
| E1 | 10.9 | | 11.1 | 0.429 | | 0.437 |
| E2 | | | 2.9 | | | 0.114 |
| E3 | 5.8 | | 6.2 | 0.228 | | 0.244 |
| E4 | 2.9 | | 3.2 | 0.114 | | 1.259 |
| e | | 0.65 | | | 0.026 | |
| e3 | | 11.05 | | | 0.435 | |
| G | 0 | | 0.075 | 0 | | 0.003 |
| H | 15.5 | | 15.9 | 0.61 | | 0.625 |
| h | | | 1.1 | | | 0.043 |
| L | 0.8 | | 1.1 | 0.031 | | 0.043 |
| N | 10° (max) | | | | | |
| s | 8° (max) | | | | | |

- (1) "D and E1" do not include mold flash or protusions.
Mold flash or protusions shall not exceed 0.15mm (0.006")
(2) No intrusion allowed inwards the leads.

OUTLINE AND MECHANICAL DATA



PowerSO36 (SLUG UP)



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